

2N7002CK,215 Information



For Reference Only

Part Number 2N7002CK,215 Manufacturer Nexperia USA Inc.

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 60V 0.3A SOT-23

Package TO-236-3, SC-59, SOT-23-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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2N7002CK,215 Specifications

Manufacturer Part Number 2N7002CK,215 Manufacturer Nexperia USA Inc. Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-236-3, SC-59, SOT-23-3 Series Automotive, AEC-Q101, TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 300mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 2.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 1.3nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 55pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 350mW (Ta) Rds On (Max) @ Id, Vgs 1.6 Ohm @ 500mA, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-236AB (SOT23) Package / Case TO-236-3, SC-59, SOT-23-3		
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Package TO-236-3, SC-59, SOT-23-3 Series Automotive, AEC-Q101, TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 300mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 2.5 V @ 250μA Gate Charge (Qg) (Max) @ Vgs 1.3nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 55pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 350mW (Ta) Rds On (Max) @ Id, Vgs 1.6 Ohm @ 500mA, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-236AB (SOT23) Package / Case TO-236-3, SC-59, SOT-23-3	Category	Discrete Semiconductor Products
SeriesAutomotive, AEC-Q101, TrenchMOS?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C300mA (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id2.5V @ 250μAGate Charge (Qg) (Max) @ Vgs1.3nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds55pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)350mW (Ta)Rds On (Max) @ Id, Vgs1.6 Ohm @ 500mA, 10VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-236AB (SOT23)Package / CaseTO-236-3, SC-59, SOT-23-3		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 300mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 2.5 V @ 250µA Gate Charge (Qg) (Max) @ Vgs 1.3nC @ 4.5 V Input Capacitance (Ciss) (Max) @ Vds 55pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 350mW (Ta) Rds On (Max) @ Id, Vgs 1.6 Ohm @ 500mA, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-236AB (SOT23) Package / Case To-236-3, SC-59, SOT-23-3	Package	TO-236-3, SC-59, SOT-23-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C300mA (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id2.5V @ 250μAGate Charge (Qg) (Max) @ Vgs1.3nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds55pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)350mW (Ta)Rds On (Max) @ Id, Vgs1.6 Ohm @ 500mA, 10VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-236AB (SOT23)Package / CaseTO-236-3, SC-59, SOT-23-3	Series	Automotive, AEC-Q101, TrenchMOS?
Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C300mA (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id2.5V @ 250μAGate Charge (Qg) (Max) @ Vgs1.3nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds55pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)350mW (Ta)Rds On (Max) @ Id, Vgs1.6 Ohm @ 500mA, 10VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-236AB (SOT23)Package / CaseTO-236-3, SC-59, SOT-23-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.6 Ohm @ 500mA, 10V Operating Temperature Mounting Type Surface Mount Supplier Device Package TO-236AB (SOT23) Package / Case 300mA (Ta) 300mA (Ta) 300mA (Ta) 300mA (Ta) 300mA (Ta) 300mA (Ta) 10V 2.5V @ 250μA 1.3nC @ 4.5V 55pF @ 25V 25V 25V 25V 25V 25V 25V 27OV TO-236AB (SOT23) TO-236-3, SC-59, SOT-23-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id2.5V @ 250μAGate Charge (Qg) (Max) @ Vgs1.3nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds55pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)350mW (Ta)Rds On (Max) @ Id, Vgs1.6 Ohm @ 500mA, 10VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-236AB (SOT23)Package / CaseTO-236-3, SC-59, SOT-23-3	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 55pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.6 Ohm @ 500mA, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-236AB (SOT23) Package / Case TO-236-3, SC-59, SOT-23-3	Current - Continuous Drain (Id) @ 25°C	300mA (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 55pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.6 Ohm @ 500mA, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-236AB (SOT23) Package / Case TO-236-3, SC-59, SOT-23-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.6 Ohm @ 500mA, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-236-3, SC-59, SOT-23-3	Vgs(th) (Max) @ Id	2.5V @ 250μA
Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 350mW (Ta) Rds On (Max) @ Id, Vgs 1.6 Ohm @ 500mA, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-236AB (SOT23) Package / Case TO-236-3, SC-59, SOT-23-3	Gate Charge (Qg) (Max) @ Vgs	1.3nC @ 4.5V
FET Feature - Power Dissipation (Max) 350mW (Ta) Rds On (Max) @ Id, Vgs 1.6 Ohm @ 500mA, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-236AB (SOT23) Package / Case TO-236-3, SC-59, SOT-23-3	Input Capacitance (Ciss) (Max) @ Vds	55pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.6 Ohm @ 500mA, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-236AB (SOT23) Package / Case TO-236-3, SC-59, SOT-23-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs1.6 Ohm @ 500mA, 10VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-236AB (SOT23)Package / CaseTO-236-3, SC-59, SOT-23-3	FET Feature	-
Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-236AB (SOT23) Package / Case TO-236-3, SC-59, SOT-23-3	Power Dissipation (Max)	350mW (Ta)
Mounting Type Surface Mount Supplier Device Package TO-236AB (SOT23) Package / Case TO-236-3, SC-59, SOT-23-3	Rds On (Max) @ Id, Vgs	1.6 Ohm @ 500mA, 10V
Supplier Device Package TO-236AB (SOT23) Package / Case TO-236-3, SC-59, SOT-23-3	Operating Temperature	150°C (TJ)
Package / Case TO-236-3, SC-59, SOT-23-3	Mounting Type	Surface Mount
	Supplier Device Package	TO-236AB (SOT23)
Report errors?	Package / Case	TO-236-3, SC-59, SOT-23-3
		Report errors?

2N7002CK,215 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

2N7002CK,215 Payment Methods





















2N7002CK,215 Shipping Methods













If you have any question about 2N7002CK,215, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com